

Assignment 4

CSE251

Fall 22

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Ans to Q.1  
part(a)

(a)  $V_G = 0 \text{ V}$

$I_{DS} = 4 \text{ mA}$

(b)  $I_{DS} = \frac{5 - V_D}{R}$

$\Rightarrow V_D = 5 - (I_{DS} \times 1) = 5 - 1 = 4 \text{ V}$

(c) Let, the circuit is in saturation region,

$$I_{DS} = \frac{k(V_{GS} - V_T)^2}{2}$$

Let,  $V_S = x$

$\Rightarrow 4 \times 2 = 4(V_{GS} - 1)^2$

$\Rightarrow (10 - V_S - 1)^2 = 2$

$\Rightarrow (-x - 1)^2 = 2 \Rightarrow x^2 - 2 \cdot (-x) \cdot 1 + 1 = 2$

$\Rightarrow x^2 + 2x + 1 = 0$

$x_1 = -1 + \sqrt{2}$

$x_2 = -1 - \sqrt{2}$

Validate:

①  $V_{ns} \geq V_T$

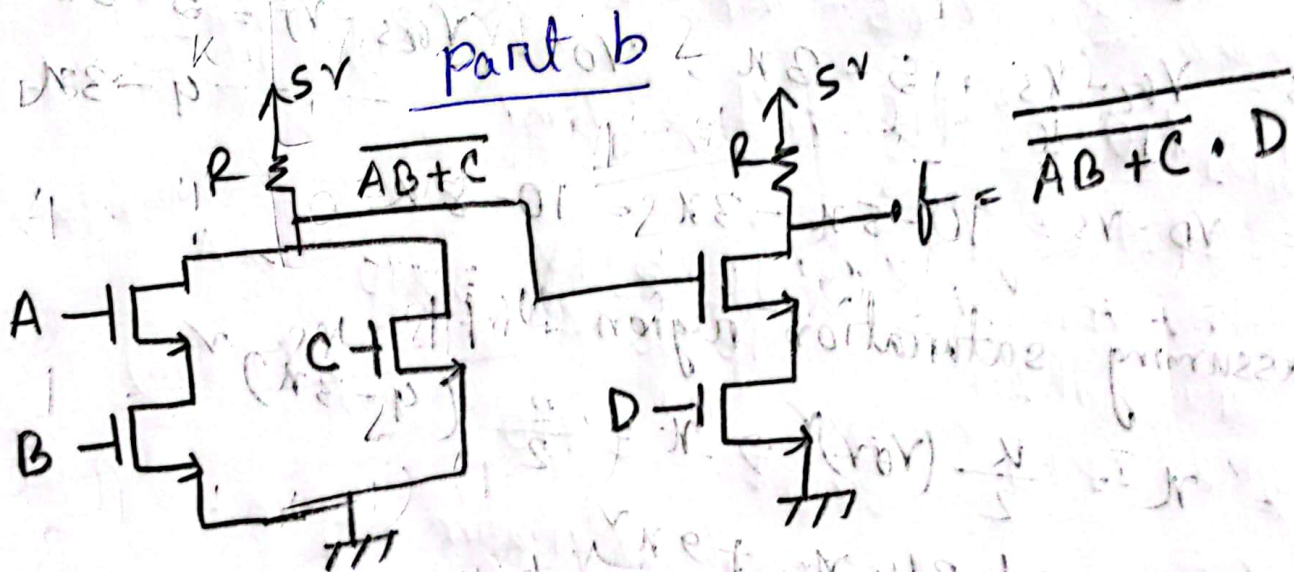
$\Rightarrow (V_n - V_T) \geq 1$

$\Rightarrow [0 - (-1 + \sqrt{2})] \geq 1 \Rightarrow 1 - \sqrt{2} \geq 1$   $[V_1 = -1 + \sqrt{2}]$

and,  $[0 - (-1 - \sqrt{2})] \geq 1 \Rightarrow 1 + \sqrt{2} \geq 1$   $[V_2 = -1 - \sqrt{2}]$

$\therefore$  This assumption was correct.

$\therefore V_S = V_2 = (-1 - \sqrt{2}) V$



$f = \overline{AB+C} \cdot D$



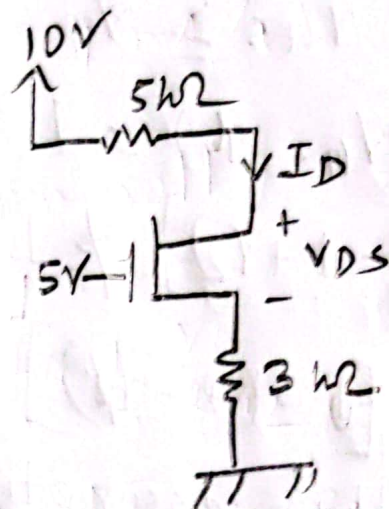
## Ans to Q 2

Let,

$$I_D = \mu$$

$$V_T = 1V$$

$$\mu = 2 \text{ mA/V}^2$$



for  $5k\Omega$ :

$$I_D = \frac{10 - V_D}{5} \Rightarrow V_D = 10 - 5I_D$$

$$\Rightarrow V_D = 10 - 5\mu$$

for  $3k\Omega$ ,

$$I_D = \frac{V_S}{3} \Rightarrow V_S = 3\mu$$

$$V_{GS} = V_G - V_S = 5 - 3\mu, \quad V_{DS} = V_D - V_S = 10 - 5\mu - 3\mu = 10 - 8\mu$$

$$V_{DS} = V_D - V_S = 10 - 5\mu - 3\mu = 10 - 8\mu$$

Now, assuming saturation region -

$$I_D = \mu = \frac{\mu}{2} (V_{GS} - V_T)^2 \Rightarrow \mu = \frac{2}{2} (4 - 3\mu)^2$$

$$\Rightarrow \mu = 16 - 24\mu + 9\mu^2$$

$$\Rightarrow 9\mu^2 - 25\mu + 16 = 0$$

$$\mu_1 = \frac{16}{9}, \quad \mu_2 = 1$$

Verify: if  $\mu_1 = \frac{16}{9} \text{ mA}$ ,

$$V_{GS} = 5 - \frac{3 \times 16}{9} = -\frac{1}{3} \neq V_T$$

Taking  $I_2 = 1 \text{ mA}$ ,

$$\textcircled{1} V_{GS} = 5 - 3 = 2 \geq V_T = 1$$

$$\textcircled{2} V_{DS} = 10 - 8 = 2 \geq V_{OV} = 4 - 3 = 1 \text{ V}$$

$$\therefore I_D = 1 \text{ mA}$$

$$V_{DS} = 2 \text{ V}$$

Ans to Q 3

Given,  $L = 0.184 \text{ m}$ ,  $W = 2.4 \text{ m}$ ,  $k_n' = 387 \times 10^{-3} \text{ mA/V}^2$

$$V_T = 0.5 \text{ V}, I_{DS} = 150 \times 10^{-3} \text{ mA}$$

In saturation region,

$$I_{DS} = \frac{k}{2} (V_{GS} - V_T)^2$$

$$\Rightarrow 150 \times 10^{-3} = \frac{4.3}{2} (V_{GS} - 0.5)^2$$

$$\Rightarrow \frac{3}{4.3} = x^2 - x + \frac{1}{4}$$

$$\Rightarrow x^2 - x + \frac{31}{172} = 0$$

$$x_1 = 0.764 \geq V_T$$

$$x_2 = 0.235 \neq V_T$$

$$\therefore V_{GS} = 0.764 \text{ V [AM]}$$

At the edge of saturation,

$$V_{DS} = V_{OV} = V_{GS} - V_T = 0.764 - 0.5 = 0.264 \text{ V}$$

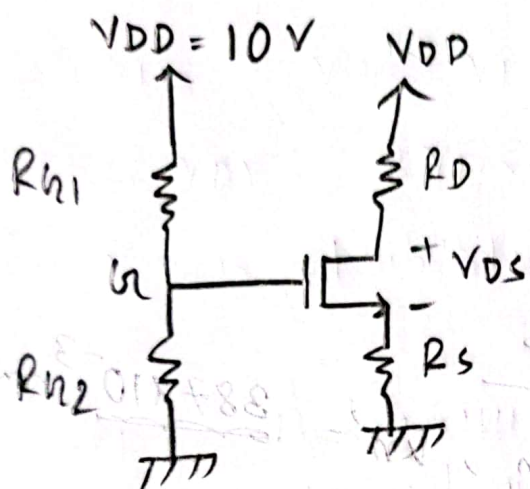
$$\therefore V_{DS} = 0.264 \text{ V [AM]}$$



Ans to q 4

Given,  $V_T = 1V$ ,  $k = k_n' \left( \frac{W}{L} \right) = 1 \text{ mA/V}^2$

$I_n = 0$



Finding the ~~therm~~ voltage:

$$\frac{V_{DD} - V_n}{R_{n1}} = I_n + \frac{V_n}{R_{n2}}$$

$$\Rightarrow R_{n2} V_{DD} - R_{n2} V_n = V_n R_{n1} + 0$$

$$\Rightarrow V_n = \frac{R_{n2} \times V_{DD}}{R_{n1} + R_{n2}}$$

$$\therefore V_n = \frac{10 \times 10^3 \times 10}{2 \times 10^3 + 10^3} = 5V \text{ (ans)}$$

$$\Rightarrow I_{R_{n1}} = \frac{V_{DD} - V_n}{R_{n1}} = \frac{10 - 5}{10 \times 10^3} = 5 \times 10^{-4} \text{ mA (ans)}$$

$$\Rightarrow I_{R_{n2}} = I_{R_{n1}} = \frac{5}{10 \times 10^3} = 5 \times 10^{-4} \text{ mA (ans)}$$

Now,  $V_n = 5V$ ; Assuming saturation region.

$$I_{DS} = \frac{k}{2} (V_{GS} - V_T)^2 \Rightarrow I_{DS} = \frac{(5 - V_{DS} - 1)^2}{2 \times 10^3} = \frac{(4 - V_{DS})^2}{2 \times 10^3} \quad \text{--- (1)}$$

$$I_{DS} = \frac{V_{DS}}{R_S} \Rightarrow I_{DS} = \frac{V_{DS}}{6} \quad \text{--- (2)}$$

From ① and ② ,

$$\frac{V_S \times 2}{6} = (4 - V_S)^2 \Rightarrow \frac{V_S}{3} = 16 + V_S^2 - 8V_S$$

$$\Rightarrow V_S = 48 + 3V_S^2 - 24V_S$$

$$\Rightarrow 3V_S^2 - 25V_S + 48 = 0$$

$$V_{S1} = \frac{16}{3} V, \quad V_{S2} = 3 V$$

$$\text{if } V_{S1} = \frac{16}{3} V, \quad V_{DS} = 5 - \frac{16}{3} = -\frac{1}{3} \neq V_T$$

$$\therefore V_S = 3 V \quad (\text{am})$$

Now,  $V_D$  :

$$\frac{10 - V_D}{6} = \frac{(4 - V_S)^2}{2} \Rightarrow \frac{10 - V_D}{3} = 16 + V_S^2 - 8V_S$$

$$\Rightarrow -V_D = 38 + 3V_S^2 - 24V_S$$

$$\Rightarrow V_D = -3V_S^2 + 24V_S - 38$$

$$\Rightarrow V_D = 7 V \quad [V_S = 3 V] \quad (\text{am})$$

$\therefore$  verify : ①  $V_{DS} = 5 - 3 = 2 V \geq V_T = 1$

②  $V_{DS} = 7 - 3 = 4 \geq (V_{DS} - V_T) = (2 - 1) = 1$

$$V_{DD} = 10 V \quad (\text{am})$$

$$I_{DS} = \frac{V_S}{6} = \frac{3}{6} = 0.5 \text{ mA} \quad (\text{am})$$



## BONUS

(i) In saturation,  $V_{DS} \geq V_{DS} - V_T$

At the edge of saturation,

$$V_{DS} = V_{DS} - V_T = V_{OV}$$

$$\Rightarrow 2V_{OV} = 2V_{DS}$$

$\therefore$  If  $V_{OV}$  is doubled,  $V_{DS}$  should be doubled too.

(ii)  $I_{D1}$  = Before current

$I_{D2}$  = changed current.

$$I_{D1} = \frac{\mu}{2} \times (V_{OV})^2 \Rightarrow (V_{OV})^2 = \frac{2 I_{D1}}{\mu} \quad \text{--- (1)}$$

$$\text{Now, } I_{D2} = \frac{\mu}{2} (2V_{OV})^2 \Rightarrow \frac{4\mu}{2} (V_{OV})^2$$

$$\therefore I_{D2} = 2\mu \times \frac{2 I_{D1}}{\mu} \quad [\text{from 1}]$$

$$\Rightarrow I_{D2} = 4 I_{D1}$$

Drain current will be multiplied by 4.

(iii) Changing  $V_{OV}$  doesn't change process parameter  $k_n'$ .  
 $k_n' = \frac{q \mu C_{ox}}{2}$  which depends on how the mosfet is made.  
However,  $k = k_n' \frac{W}{L}$ ,  $k$  will change if  $V_{OV}$  is changed as the  $W$  and  $L$  depends on  $V_{OV}$ .